



SEMITOP[®] 2

IGBT Module

SK50GB065

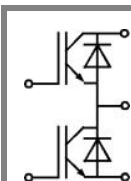
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N-channel homogeneous silicon structure (NPT-Non-Punch-Through IGBT)
- Low tail current with low temperature dependence
- Low threshold voltage

Typical Applications

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



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Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	600	V
I_C	$T_j = 125\text{ °C}$	$T_s = 25\text{ °C}$	54 A
		$T_s = 80\text{ °C}$	40 A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	60	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 300\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	10	μs
Inverse Diode			
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	64 A
		$T_s = 80\text{ °C}$	48 A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$		A
I_{FSM}	$t_p = 10\text{ ms}$; half sine wave $T_j = 150\text{ °C}$	200	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +150	$^{\circ}\text{C}$
T_{stg}		-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1,4\text{ mA}$	3	4	5	V	
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$ $T_j = 25\text{ °C}$			0,0044	mA	
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$ $T_j = 25\text{ °C}$			240	nA	
V_{CE0}			$T_j = 25\text{ °C}$	1,1	V	
			$T_j = 125\text{ °C}$	1,1	V	
r_{CE}	$V_{GE} = 15\text{ V}$		$T_j = 25\text{ °C}$	15	$\text{m}\Omega$	
			$T_j = 125\text{ °C}$	19	$\text{m}\Omega$	
$V_{CE(sat)}$	$I_{Cnom} = 60\text{ A}$, $V_{GE} = 15\text{ V}$		$T_j = 25\text{ °C}_{chiplev.}$	2	2,5	V
			$T_j = 125\text{ °C}_{chiplev.}$	2,2		V
C_{ies}	$V_{CE} = 25$, $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		3,2	nF	
C_{oes}			0,3	nF		
C_{res}			0,18	nF		
$t_{d(on)}$	$R_{Gon} = 16\ \Omega$	$V_{CC} = 300\text{ V}$ $I_C = 40\text{ A}$		60	80	ns
t_r				30	40	ns
E_{on}	$R_{Goff} = 16\ \Omega$	$T_j = 125\text{ °C}$ $V_{GE} = \pm 15\text{ V}$		1,1	1,4	mJ
$t_{d(off)}$				220	280	ns
t_f				20	26	ns
E_{off}				0,7	0,9	mJ
$R_{th(j-s)}$	per IGBT			0,85	K/W	



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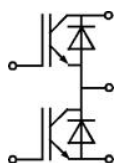
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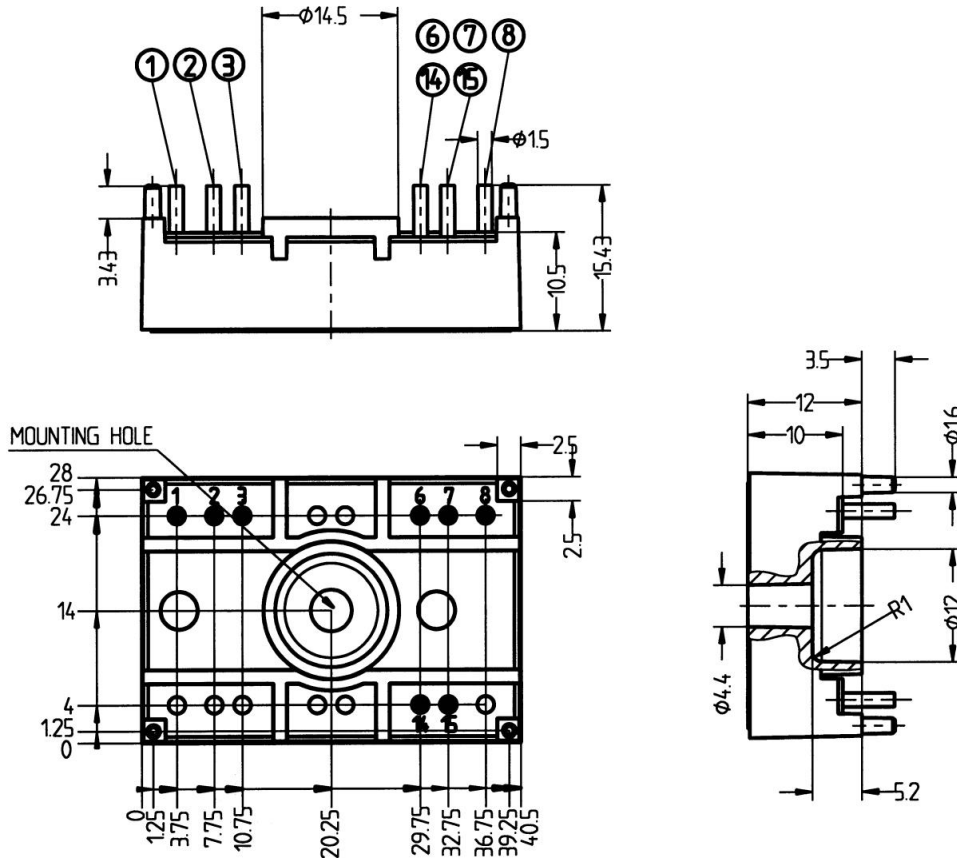
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Characteristics

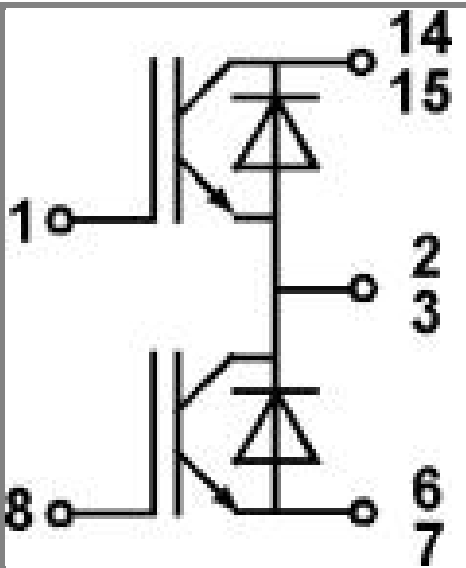
Symbol	Conditions	min.	typ.	max.	Units	
Inverse Diode						
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$		$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,45	1,7	V
			$T_j = 150 \text{ }^\circ\text{C}_{chiplev.}$	1,4	1,75	V
V_{F0}			$T_j = 25 \text{ }^\circ\text{C}$			V
			$T_j = 125 \text{ }^\circ\text{C}$	0,85	0,9	V
r_F			$T_j = 25 \text{ }^\circ\text{C}$			mΩ
			$T_j = 125 \text{ }^\circ\text{C}$	11	16	mΩ
I_{RRM}	$I_F = 50 \text{ A}$				A	
Q_{rr}	$di/dt = -1000 \text{ A}/\mu\text{s}$				μC	
E_{rr}	$V_{CC} = 300\text{V}$				mJ	
$R_{th(j-s)D}$	per diode			1,1	K/W	
M_s	to heat sink			2	Nm	
w			19		g	

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



Case T32 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 32

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